



BF 257 · BF 258 · BF 259

查询BF257供应信息

捷多邦, 专业PCB打样工厂, 24小时加急出货

NPN HIGH VOLTAGE VIDEO AMPLIFIER

MICRO ELECTRONICS

THE BF257, BF258, BF259 ARE NPN SILICON PLANAR TRANSISTORS DESIGNED FOR HIGH VOLTAGE VIDEO OUTPUT STAGES IN BLACK-AND-WHITE AND COLOUR TV-RECEIVERS.

CASE TO-39



C E B

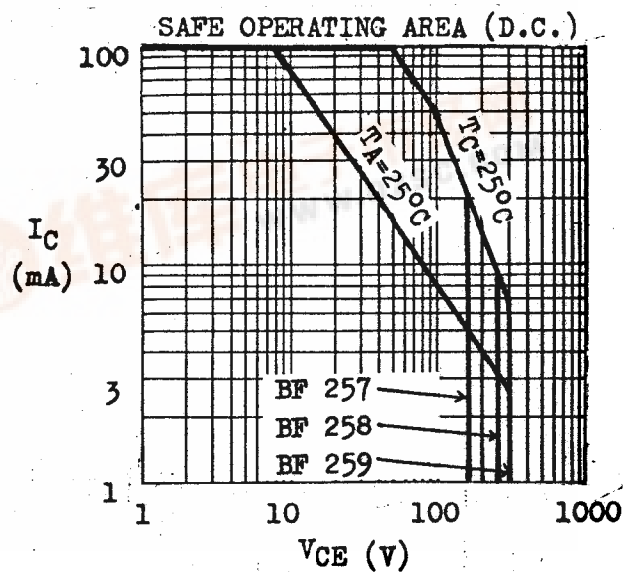
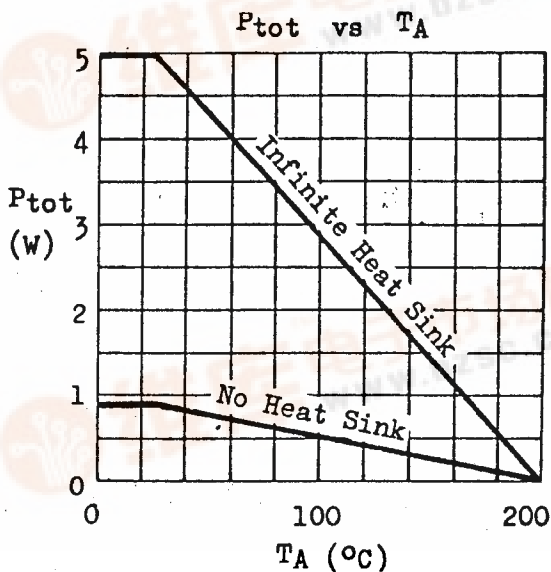
ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CBO}	160V	250V	300V
Collector-Emitter Voltage	V_{CEO}	160V	250V	300V
Emitter-Base Voltage	V_{EB0}		5V	
Collector Current	I_C		100mA	
Total Power Dissipation @ $T_C \leq 25^\circ C$	P_{tot}		5W	
@ $T_A \leq 25^\circ C$			800mW	
Operating Junction & Storage Temperature	T_j, T_{stg}		-65 to 200°C	

BF257	BF258	BF259
160V	250V	300V
160V	250V	300V
	5V	
	100mA	
	5W	
	800mW	
	-65 to 200°C	

THERMAL RESISTANCE

Junction to Case	θ_{jc}	35°C/W	max.
Junction to Ambient	θ_{ja}	220°C/W	max.



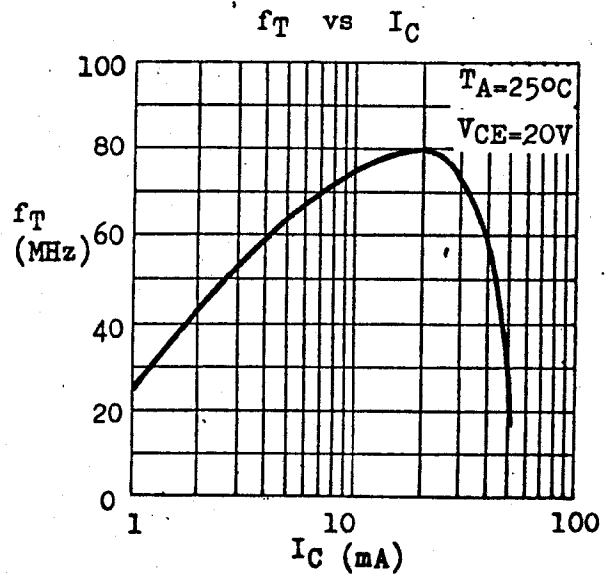
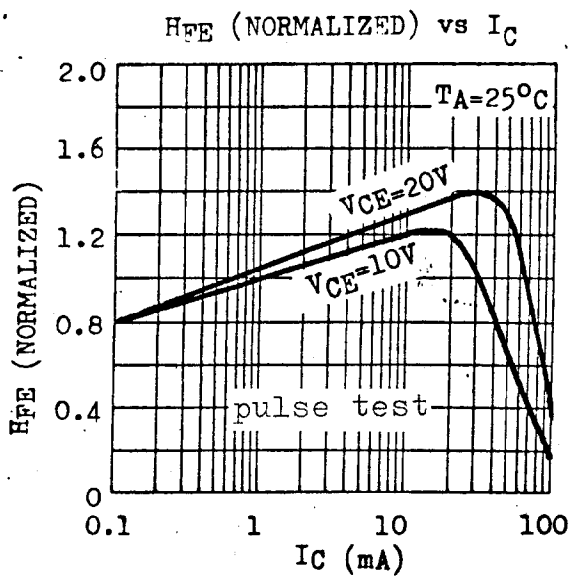
MICRO ELECTRONICS LTD.

38 HUNG TO ROAD, KWUN TONG, HONG KONG. TELEX 43510
 KWUN TONG P. O. BOX 69477 CABLE ADDRESS "MICROTRON"
 TELEPHONE:- 3-430181-6 3-893363, 3-892423

FAX: 3-410321

PARAMETER	SYMBOL	BF257		BF258		BF259		UNIT	TEST CONDITIONS
		MIN	MAX	MIN	MAX	MIN	MAX		
ollector-Base Breakdown Voltage	BV_{CBO}	160		250		300		V	$I_C=0.1mA$ $I_E=0$
ollector-Emitter Breakdown Voltage	LV_{CEO}^*	160		250		300		V	$I_C=10mA$ $I_B=0$
mitter-Base Breakdown Voltage	BV_{EBO}	5		5		5		V	$I_E=0.1mA$ $I_C=0$
ollector Cutoff Current	I_{CBO}		50		50		50	nA	$V_{CB}=100V$ $I_E=0$
								nA	$V_{CB}=200V$ $I_E=0$
								nA	$V_{CB}=250V$ $I_E=0$
mitter Cutoff Current	I_{EBO}		50		50		50	nA	$V_{EB}=3V$ $I_C=0$
.C. Current Gain	H_{FE}^*	25		25		25			$I_C=30mA$ $V_{CE}=10V$
ollector-Emitter Saturation Voltage	$V_{CE(sat)}^*$		1		1		1	V	$I_C=30mA$ $I_B=6mA$
urrent Gain-Bandwidth Product	f_T	50		50		50		MHz	$I_C=15mA$ $V_{CE}=20V$
ollector-Base Capacitance	C_{cb}		5		5		5	pF	$V_{CB}=30V$ $I_E=0$ $f=1MHz$

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%



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